

Features and Benefits

- Supply voltage, V_{BB}, 36 V maximum
- Maximum DC current 3 A continuous, 6 A pulsed (1 kHz, duty cycle < 1%, pulse width < 10 μs)
- $R_{DS(on)} = 300 \text{ m}\Omega$ maximum, at $T_J = 125^{\circ}\text{C}$
- Operation modes: forward, reverse, brake (high- or lowside freewheeling current circulation)
- Output disable pin (DI pin)
- Protections:
- ^a Overvoltage protection (OVP), 36 V minimum
- Overcurrent protection (OCP), 3 A typical
- Overcurrent limitation (OCL), 6 A typical
- Externally adjustable delay timer to halt OCL
- ^o Thermal shutdown protection (TSD), 151°C minimum
- Undervoltage lockout on V_{BB} (UVLO), 4.2 V minimum
- Open load detection at startup
- Diagnosis output linked to OVP, OCP, TSD, UVLO, and open load detection, at startup and in operation

Package: 16 pin HSOP with exposed thermal pad and tabs

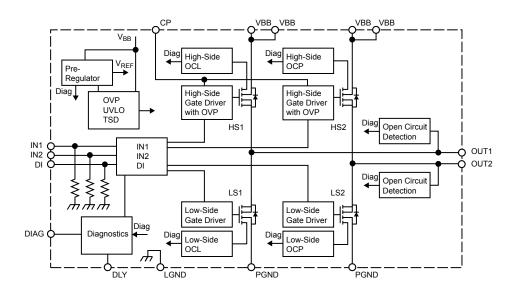


The SPF7302 is a fully protected, single chip full-bridge driver IC for DC brush motor applications. The various protection circuits integrated are: overvoltage protection (OVP); overcurrent protection (OCP) with latch, which is adapted to the DMOSFETs in each full bridge; undervoltage lockout (UVLO); open load detection; and overcurrent limitation.

The package is a thermally enhanced 16-pin HSOP power package with an exposed thermal pad on the bottom side of the package.

Not to scale

Functional Block Diagram



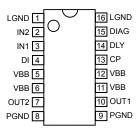
Selection Guide

Part Number Package		Packing
SPF7302	Thermally enhanced surface mount (HSOP), 16-pin	Minimum quantity 1400 pieces

Absolute Maximum Ratings at T_A = 25°C

Characteristic	Symbol	Notes	Rating	Unit	
Supply Voltage	V _{BB}		-0.3 to 36	V	
IN1, IN2, DI, and DLY Pin Input Voltage	V _x		-0.3 to 6	V	
Output Current	Io		±3	Α	
Output Current	I _{Opeak}	Continuous: 1 kHz, duty cycle <1%; pulse: < 10 µs	±6	Α	
DIAG Pin Output Voltage	V_{DIAG}		-0.3 to 6	V	
DIAG Pin Input Current	I _{DIAG}	DIAG pin sink current	-2	mA	
CP Pin Voltage	V _{CP}		-0.3 to 36	v	
	P _{D1}	With infinite heatsink	39		
Power Dissipation	P _{D2}	Mounted on glass epoxy PCB, 50 mm×74 mm×1.6 mm; 0.5 oz copper (18 µm thick) exposed copper area	4	W	
Junction Temperature	TJ		-40 to 150	°C	
Operating Ambient Temperature	T _A		-40 to 105	°C	
Storage Temperature	T _{stg}		40 to 150	°C	
Thermal Resistance, Junction to Case	R _{θJC}	Mounted on glass epoxy PCB, 50 mm × 74 mm × 1.6 mm;	3.2	°C/W	
Thermal Resistance, Junction to Ambient	R _{θJA}	0.5 oz copper (18 µm thick) exposed copper area	31	°C/W	

Pin-out Diagram



Terminal List Table

Number	1 LGND Logic GND 2 IN2 Input pin 2 3 IN1 Input pin 1 4 DI Disable pin					
1	LGND	Logic GND				
2	IN2	Input pin 2				
3	IN1	Input pin 1				
4	DI	Disable pin				
5	VBB Supply input voltage					
6	6 VBB Supply input voltage					
7	1171					
8	8 PGND Power GND					
9	9 PGND Power GND					
10	OUT1	Output 1				
11	VBB	Supply input voltage				
12	VBB	Supply input voltage				
13	13 CP Charge pump capacitor pin					
14	14 DLY Overcurrent limitation delay setting input pin					
15	DIAG	Diagnostics output pin				
16	LGND	Logic GND				

All performance characteristics given are typical values for circuit or system baseline design only and are at the nominal operating voltage and an ambient temperature, T_A , of 25°C, unless otherwise stated.

SPF7302

ELECTRICAL CHARACTERISTICS¹ valid at T_J = -30° C to 125°C, V_{BB} = 14 V, V_{DI} = 5 V, C_{CP} = 47 nF, R_{DIAG} = 5.1 k Ω , unless otherwise specified

Characteristic	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Supply Voltage	V_{BB}		6	_	18	V
OUTy Pin Lookaga Current	I _{leakHS}		-1	_	-	mA
OUTx Pin Leakage Current	I _{leakLS}		-	-	1	mA
	R _{DS(ON_1H}	I _{OUT} = 1 A	_			mΩ
DMOSFET On Resistance	R _{DS(ON)_2H}	I _{OUT} = 3 A	_	_	18 - 1	mΩ
DIVIOSPET Off Resistance	R _{DS(ON)_1L}	I _{OUT} = 1 A	_	_	300	mΩ
	R _{DS(ON)_2L}	I _{OUT} = 3 A	_	_	300	mΩ
	V _{F_H1}	I _{OUT1} = 1 A	_	1.0	2.0	V
DMOSFET Body Diode Forward Voltage	V _{F_H2}	I _{OUT2} = 1 A	_	1.0	2.0	V
DIVIOSPET Body Diode Forward Voltage	V _{F_L1}	I _{OUT1} = -1 A	_	1.0	- 1 300 300 300 300 2.0 2.0 2.0 2.0 2.0 4.5 4.5 4.5 4.5 8.0 8.0 8.0 8.0 5.3 1.5 200 1 - 0.4 - 3 3 15 15 2	V
	V _{F_L2}	I _{OUT2} = -1 A	_	1.0	2.0	V
Quiescent Current	I _{BB}		_	7	-	mA
	I _{OCL_H1}		2.0	3.0	18	Α
Oversurrent Limit (OCL)	I _{OCL_H2}	$T_J = -40^{\circ}$ C to 150°C, $I_{OCL} < I_{OCP}$; guaranteed by	2.0	3.0		Α
Overcurrent Limit (OCL)	I _{OCL_L1}	18				
	I _{OCL_L2}		2.0	3.0	4.5	Α
	I _{OCP_H1}		4.5	6.0	8.0	Α
Overcurrent Protection (OCP)	I _{OCP_H2}	$T_J = -40^{\circ}$ C to 150°C, $I_{OCL} < I_{OCP}$; guaranteed by	4.5	6.0	18 V - mA 1 mA 300 mΩ 300 mΩ 300 mΩ 300 mΩ 2.0 V 2.0 V 2.0 V 2.0 V - mA 4.5 A 4.5 A 4.5 A 4.5 A 8.0 A 8.0 A 8.0 A 8.0 A 8.0 A 8.0 A 1.5 V 200 μA 1 μA - V 0.4 V - μA 3 mA 15 μs 15 μs 2 μs	Α
Overcurrent Protection (OCP)	I _{OCP_L1}	design	6	Α		
		Α				
INIA INIA DI and DI V Din Input Voltago	V _{x_H}			_	5.3	V
IN1, IN2, DI, and DLY Pin Input Voltage	V _{x_L}		-0.3	_	1.5	V
IN1, IN2, DI, and DLY Pin Input Current	I _{x_H}	V _{DLY} = 5 V	_	100	200	μΑ
in 1, in 2, bi, and bet Fill input current	I _{x_L}	V _{DLY} = 0 V	– 1	_	1	μΑ
DIAG Pin Output Voltage	V _{DIAG_H}	V _{CC} = 5 V	4.0	_	_	V
DIAG FIII Output Voltage	V _{DIAG_L}	I _{sink} = 2 mA	_	_	0.4	V
DIAG Pin Output Current	I _{DIAG_H}	V _{CC} = 5 V, DIAG pin source current	-250	_	1	μΑ
DIAG FIII Output Current	I _{DIAG_L}	V _{CC} = 5 V, DIAG pin sink current, V _{DIAG} = 2 V	_	_	3	mA
IN1 and IN2 Pin Input Propagation Time	t _{INx_ON}	Delay from V _{INx} = 2 V→V _{OUTx} × 0.2	_	7	15	μs
in and in Fin input Fropagation fille	t _{INx_OFF}	Delay from V _{INx} = 1.5 V→V _{OUTx} × 0.8	_	7	15	μs
Output Rise Time	t _{rx}		_	0.5	2	μs
Output Fall Time	t _{fx}		_	0.5	2	μs

Continued on the next page...

ELECTRICAL CHARACTERISTICS¹ (continued) valid at $T_J = -30$ °C to 125°C, $V_{BB} = 14$ V, $V_{DI} = 5$ V, $C_{CP} = 47$ nF,

 $R_{DIAG} = 5.1 \text{ k}\Omega$, unless otherwise specified

Characteristic Symbol Test Conditions		Min.	Тур.	Max.	Unit	
DLY Pin Threshold Voltage	Pin Threshold Voltage V _{DLY(th)} Overcurrent limitation (OCL) activa		1.4	1.6	1.8	V
DLY Pin Sourcing Current ²	I _{DLY}		15	30	60	μA
UVLO Releasing Voltage	V _{UVLO_OFF}		_	-	5.2	V
UVLO Activating Voltage	V _{UVLO_ON}		4.2	_	_	V
UVLO Hysteresis	V _{UVLOhys}		_	0.2	-	V
OVP Protection Activating Voltage	V _{OVP_ON}		36	_	42	V
OVP Protection Releasing Voltage	V _{OVP_OFF}		32	-	38	V
OVP Hysteresis	V _{OVPhys}		_	5	_	V
Thermal Shutdown Activating Temperature ³	T _{TSD_ON}	Starts at 165°C typical; guaranteed by design	151	165	_	°C
Thermal Shutdown Releasing Temperature ³	T _{TSD_OFF}	Guaranteed by design	136	150	_	°C
Thermal Shutdown Hysteresis ³	T _{TSDhys}	Guaranteed by design	_	15	_	°C

 $^{^{1}}$ The parameters at T_J = -40° C to 150° C are specified by design. The actual production tests are done at 25° C and 125° C.

Motor Control Truth Table¹

Reference	Reference Status		Input			Output			DMOSFET status			
Number			IN1	IN2	OUT1	OUT2	DIAG	HS1	LS1	HS2	LS2	
1	Forward rotation ²	Н	Н	L	Н	L	Н	ON	OFF	OFF	ON	
2	Reverse rotation ²	Н	L	Н	L	Н	Н	OFF	ON	ON	OFF	
3	Low-side freewheeling	Н	L	L	L	L	Н	OFF	ON	OFF	ON	
4	High-side freewheeling	Н	Н	Н	H	Н	Н	ON	OFF	ON	OFF	
5	Output disabled	L	Χ	X	Z	Z	Н	OFF	OFF	OFF	OFF	
6	Overcurrent limitation (OCL) active (HS1)	Н	Н	Х	Н	Х	Н	ON	OFF	Х	Χ	
7	Overcurrent limitation (OCL) active (HS2)	Н	X	Н	X	Н	Н	X	Χ	ON	OFF	
8	Overcurrent limitation (OCL) active (LS1)	Н	L	X	L	X	Н	OFF	ON	X	X	
9	Overcurrent limitation (OCL) active (LS2)	Н	Χ	L	X	L	Н	X	Χ	OFF	ON	
10	Overcurrent protection with latch (OCP) active (HS1)	Н	Н	X	Z	Z	L	OFF	OFF	OFF	OFF	
11	Overcurrent protection with latch (OCP) active (HS2)	Н	Χ	Н	Z	Z	L	OFF	OFF	OFF	OFF	
12	Overcurrent protection with latch (OCP) active (LS1)	Н	L	X	Z	Z	L	OFF	OFF	OFF	OFF	
13	Overcurrent protection with latch (OCP) active (LS2)	Н	Χ	L	Z	Z	L	OFF	OFF	OFF	OFF	
14	Undervoltage lockout (UVLO) protection active	X	Χ	X	Z	Z	L	OFF	OFF	OFF	OFF	
15	Overvoltage protection (OVP) active	X	Χ	X	X	X	L	X	Χ	X	Χ	
16	Open load detected at startup	L	Χ	Χ	X	X	L	OFF	OFF	OFF	OFF	
17	Open load detected in operation	Н	Χ	Χ	X	X	L	X	Χ	X	Χ	
18	Thermal shutdown protection (TSD) active	X	Χ	Χ	Z	Z	L	OFF	OFF	OFF	OFF	

¹X is "don't care," Z is high impedance.

²The individual overcurrent limitation of each DMOSFET is masked during the delay period. Therefore, ensure proper thermal design for dissipating transient temperature increase caused by current during this period.

³TSD (thermal shutdown protection starts at 165°C typical, and it is specified by design.

²"Forward" and "reverse" only indicate opposite relative direction.

Switching Operation Timing Charts

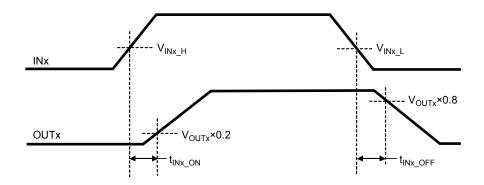


Figure 1. Output Delay Time

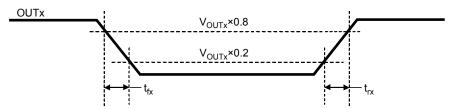
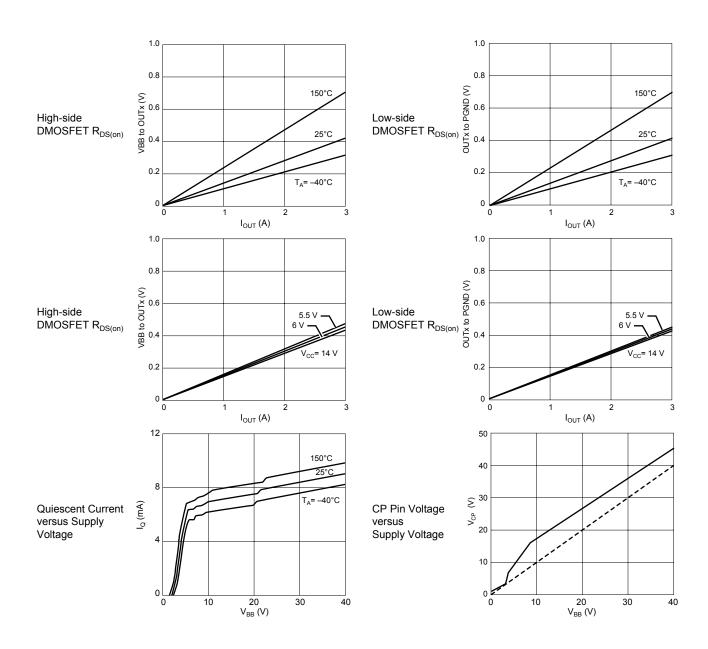
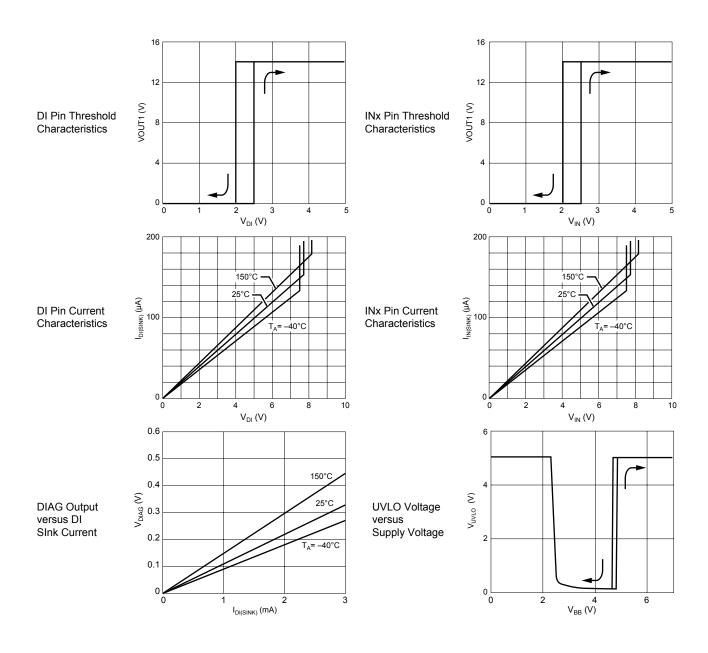


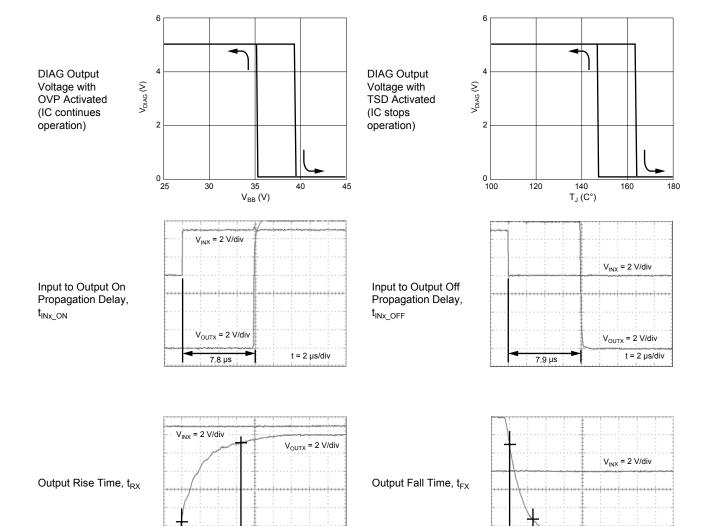
Figure 2. Output Switching Time

Characteristic Performance

T_A = 25°C unless otherwise specified





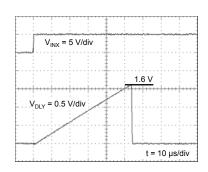


 $V_{OUTX} = 2 V/div$

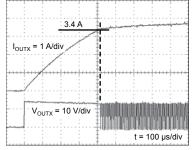
t = 100 ns/div

t = 50 ns/div

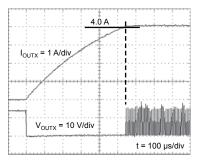
DLY Voltage versus INx Pin Voltage



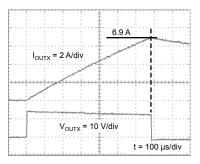
High-side DMOSFET OCL Operation Example



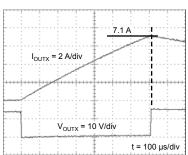
Low-side DMOSFET OCL Operation Example



High-side DMOSFET OCP Operation Example



Low-side DMOSFET OCP Operation Example



Protection Function Operation

Current Limitation and Overcurrent Protection

The overcurrent limit is adapted to each DMOSFET, and is activated when the drain current reaches 3 A typical. After that, it is followed by a 3 μ s typical off-time, and then it restarts automatically.

Overcurrent protection is activated when the drain current reaches 6 A typical within 3 μ s, as shown in figure 3. It shuts down the IC in a latch mode. Setting the DI pin to logic low level resets the internal logic circuit and releases the latch.

DIAG Pin and Open Load Detection Behavior

Open load detection does not operate until after the output voltage of OUT1 (V_{OUT1}) reaches about $V_{BB}-2$ V. If an open load is detected, the DIAG signal goes high. The process of open load detection is shown in figure 4:

- A. During this period, UVLO is activated and DIAG stays low.
- B. If a filtering capacitor is used at the outputs, it causes a delay of open load detection. (Refer to figure 5 for the relationship of the delay versus the filtering capacitor value.)
- C. The open load detection period starts functioning. Raising DI input above V_{DI_H} (threshold), that is, by activating the IC, clears the DIAG signal. Therefore, the open load condition must be checked before the time of that event.

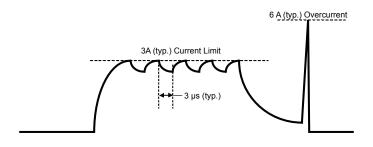


Figure 3. Behavior of Current Limitation and Overcurrent Protection function

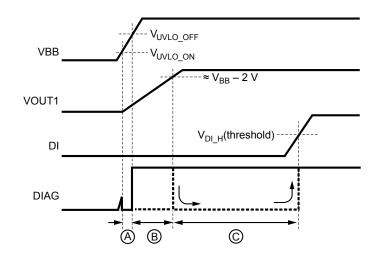


Figure 4. Open Load Detection

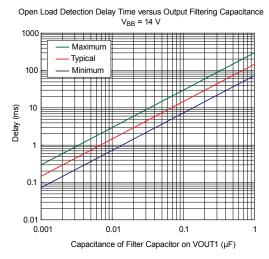


Figure 5. Delay to Open Load protection activation versus value of external capacitor on the output pins

Open load detection during normal operation of the IC is done by checking the negative potential of the output.

Referring to figure 6, during normal operation, recirculation current causes the output to be below GND. The IC checks the output voltage during 2.5 μ s typical, just after the falling edge of the corresponding IN signal, and if it does not detect the negative potential, DIAG is asserted after the 2.5 μ s detection period. During the 2.5 μ s period, the DIAG pin is set to high because the internal circuit is reset during that period (see the arrows marked *A* in figure 6).

Open load detection operates differently during startup of the IC. The overcurrent limitation deactivated period occurs immediately after DI is asserted. Therefore, in order to repeat OCL deactivation, recycle DI.

During this period, overcurrent protection (OCP) is still active. (With regard to OCL delay, see also note 2 to the Electrical Characteristics table.)

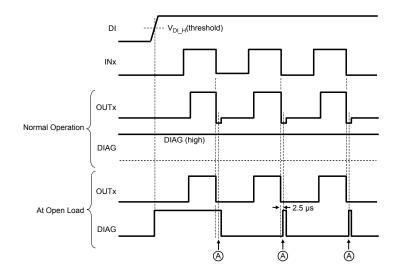


Figure 6. Open load detection in normal operation

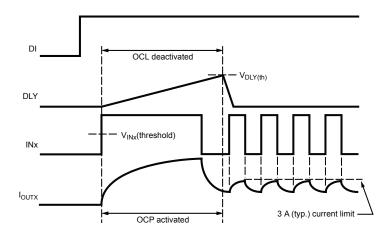


Figure 7. DLY pin effect at startup

Application Information

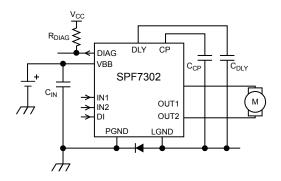


Figure 8. Typical application circuit. Recommended components are:

 $\begin{array}{cc} C_{CP} & 48 \text{ nF} \\ \\ C_{DLY} & 0.1 \text{ } \mu\text{F} \\ \\ R_{DIAG} & 3.3 \text{ } k\Omega \end{array}$

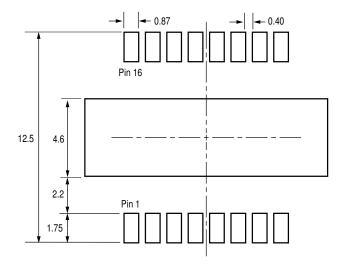


Figure 9. Recommended Solder Pad Layout, dimensions in mm

Thermal Design

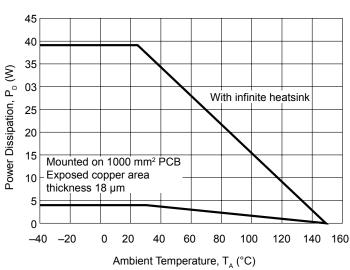


Figure 10. Power Dissipation Derating Curve

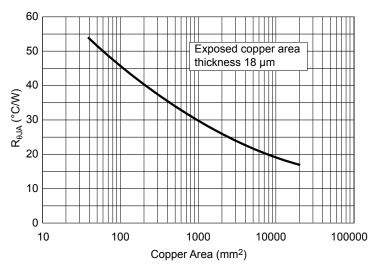


Figure 11. Thermal Resistance versus PCB Copper Area

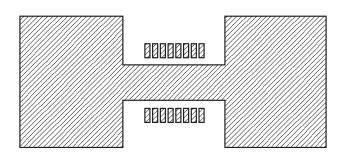


Figure 12. Test PCB Land Pattern

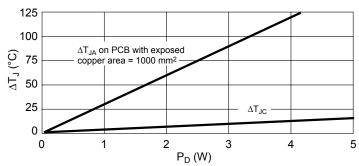


Figure 13. Thermal Performance

Approximate power dissipation, P_D , in normal operation is calculated by equation 1, and the junction temperature, T_J , is estimated by equation 2 or 3. Figure 13 shows example data of ΔT_J versus P_D . Note: a final thermal evaluation should be done under actual application conditions, taking into account actual PCB and load conditions.

$$\begin{split} P_D &\approx V_{BB} \times I_{BB1} + \ (V_{satH} + V_{satL}) \times I_{OM} \times D_{ON} \\ &+ (V_{satL(H)} + V_F) \times I_{OM} \times D_{OFF} \end{split} \tag{1}$$

where

V_{BB} is the supply voltage (battery voltage),

I_{BB1} is the circuit current during operation,

V_{satH} is the high-side saturation voltage,

V_{satL} is the low-side saturation voltage,

V_F is the freewheeling diode forward voltage,

I_{OM} is the motor current,

D_{ON} is the IN1 and IN2 duty cycle (proportion on), and

 D_{OFF} is the IN1 and IN2 proportion off ($D_{ON} + D_{OFF} = 100\%$).

To calculate T_I:

$$T_{J} = R_{\theta JA} \times P_{D} + T_{A} \tag{2}$$

or

$$T_{\rm J} = T_{\rm P} + R_{\rm \theta JC} (3.2^{\circ} \text{C/W}) \times P_{\rm D}$$
 (3)

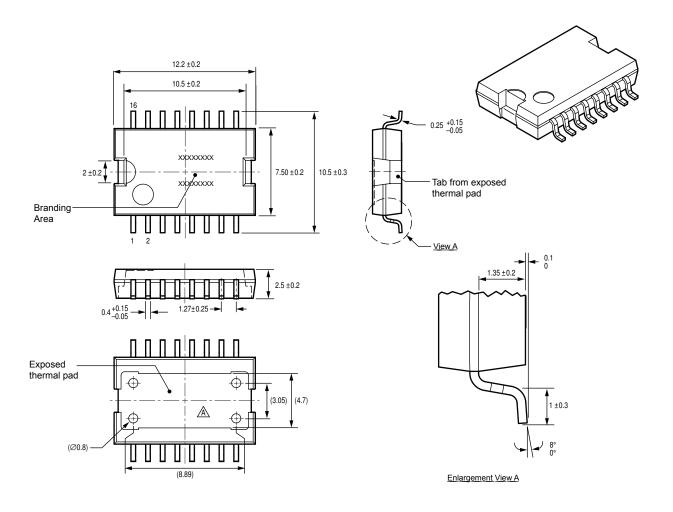
where:

 $R_{\theta JA}$ can be obtained from figure 11, and

T_P is the temperature at the exposed thermal pad of the device.

SANKEN ELECTRIC CO., LTD.

Package Outline Drawing, 16 Pin HSOP



Package: HSOP-16

Dimensions in millimeters

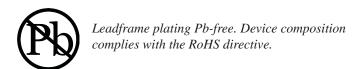
Branding codes (exact appearance at manufacturer discretion):

1st line, type: SPF7302 2nd line, lot: *YMDD*

Where: Y is the last digit of the year of manufacture

M is the month (1 to 9, 0, N, D)

DD is the date



Because reliability can be affected adversely by improper storage environments and handling methods, please observe the following cautions.

Cautions for Storage

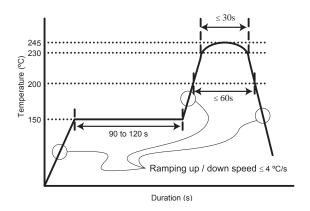
- Ensure that storage conditions comply with the standard temperature (5°C to 35°C) and the standard relative humidity (around 40% to 75%); avoid storage locations that experience extreme changes in temperature or humidity.
- Avoid locations where dust or harmful gases are present and avoid direct sunlight.
- Reinspect for rust on leads and solderability of the products that have been stored for a long time.

Cautions for Testing and Handling

When tests are carried out during inspection testing and other standard test periods, protect the products from power surges from the testing device, shorts between the product pins, and wrong connections. Ensure all test parameters are within the ratings specified by Sanken for the products.

Soldering

- When soldering the products, please be sure to minimize the working time, and any soldering iron should be kept at a distance from the body of the product.
- The number of reflow procedures is restricted to two only. Device reliability and appearance are guaranteed within the temperature profile below, after storage conditions of up to 168 hours at T_A = 85°C and RH = 85%.



Solder Reflow Profile

Electrostatic Discharge

- When handling the products, the operator must be grounded. Grounded wrist straps worn should have at least 1 M Ω of resistance from the operator to ground to prevent shock hazard, and it should be placed near the operator.
- Workbenches where the products are handled should be grounded and be provided with conductive table and floor mats
- When using measuring equipment such as a curve tracer, the equipment should be grounded.
- When soldering the products, the head of soldering irons
 or the solder bath must be grounded in order to prevent
 leak voltages generated by them from being applied to the
 products.
- The products should always be stored and transported in Sanken shipping containers or conductive containers, or be wrapped in aluminum foil.

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